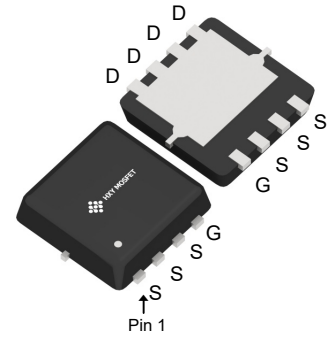


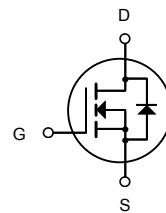


Description

The HXY30N06DF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



DFN3X3-8L



N-Channel MOSFET

General Features

$V_{DS} = 60V$ $I_D = 15A$

$R_{DS(ON)} < 40m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HXY30N06DF	DFN3X3-8L	HXY MOSFET	5000

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	15	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	11	A
I_{DM}	Pulsed Drain Current ²	46	A
EAS	Single Pulse Avalanche Energy ³	25.5	mJ
I_{AS}	Avalanche Current	20	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	34.7	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ C/W$



Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60V, V_{GS}=0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.6	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS}=10V, I_D=5A$	-	28	40	m Ω
		$V_{GS}=4.5V, I_D=3A$	-	36	50	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0\text{MHz}$	-	1148	-	pF
C_{oss}	Output Capacitance		-	58.5	-	pF
C_{rss}	Reverse Transfer Capacitance		-	49.4	-	pF
Q_g	Total Gate Charge	$V_{DS}=30V, I_D=2.5A,$ $V_{GS}=10V$	-	20.3	-	nC
Q_{gs}	Gate-Source Charge		-	3.7	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	5.3	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=30V, I_D=5A,$ $R_G=1.8\Omega, V_{GS}=10V$	-	7.6	-	ns
t_r	Turn-on Rise Time		-	20	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	15	-	ns
t_f	Turn-off Fall Time		-	24	-	ns
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	15	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=5A$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=5A, di/dt=100A/\mu s$	-	29	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	43	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=30V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega, I_{AS}=8.7A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$



Typical Characteristics

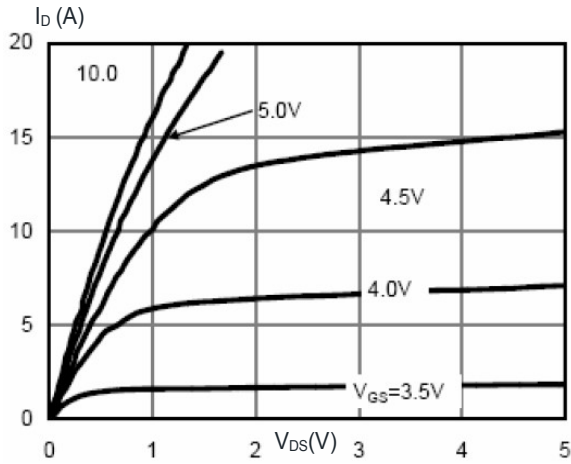


Figure 1: Output Characteristics

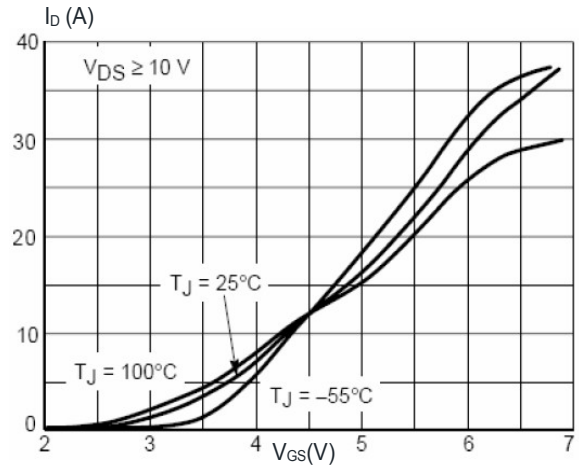


Figure 2: Typical Transfer Characteristics

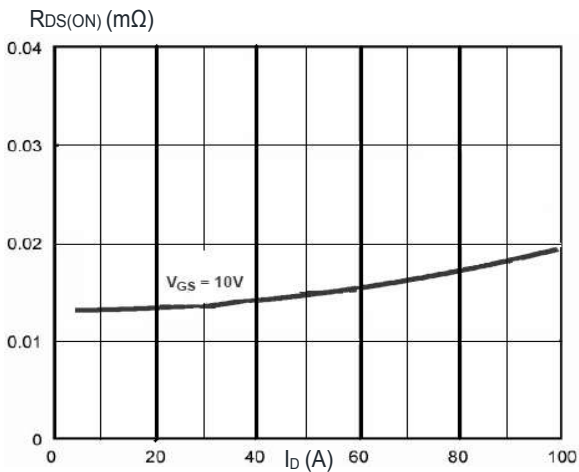


Figure 3: Rdson- Drain Current

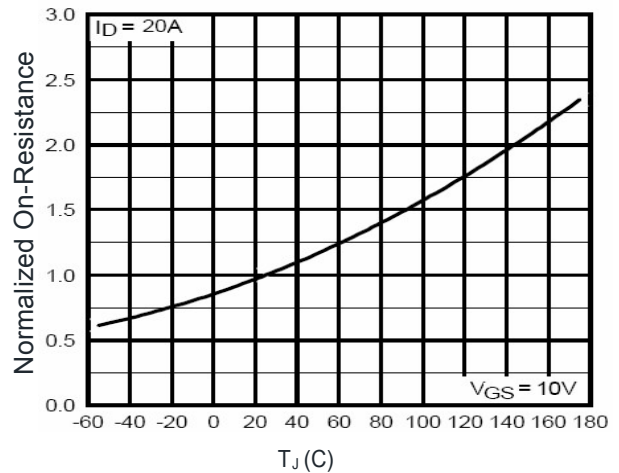


Figure 4: Rdson-Junction Temperature

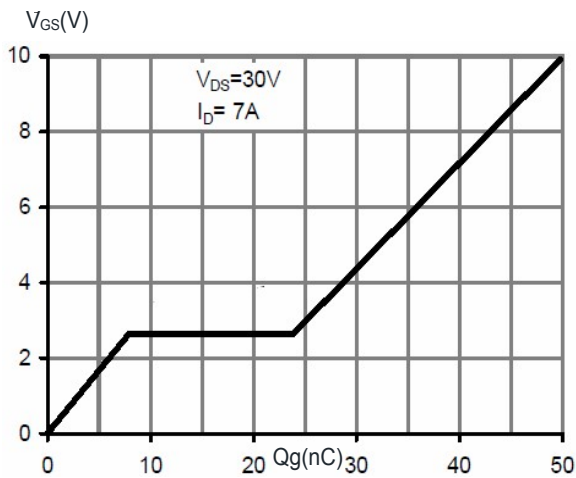


Figure 5: Gate Charge

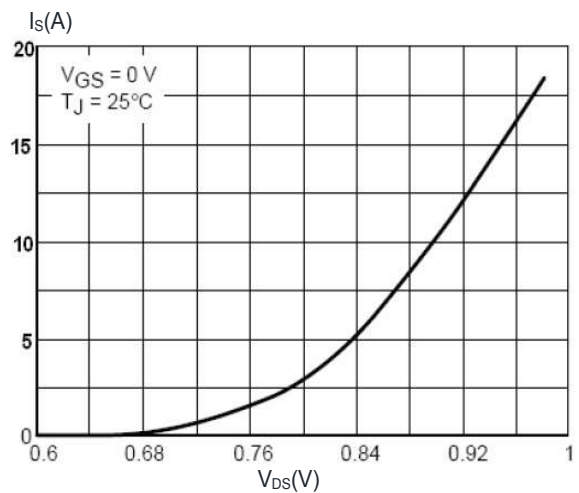


Figure 6: Source-Drain Diode Forward

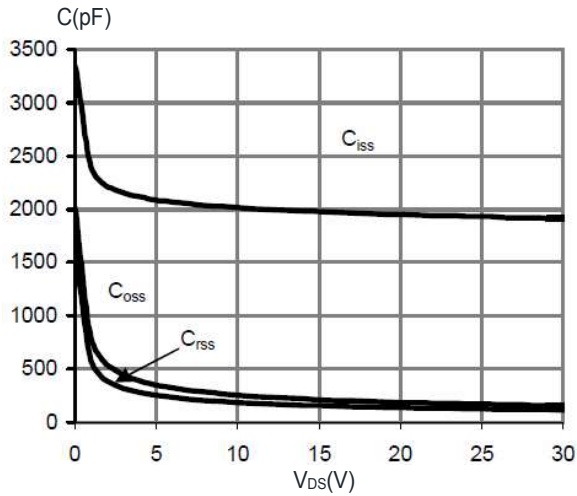


Figure 7: Capacitance vs Vds

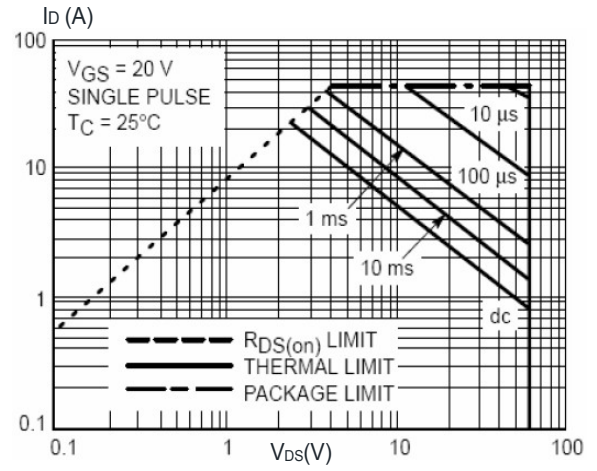


Figure 7: Safe Operation Area

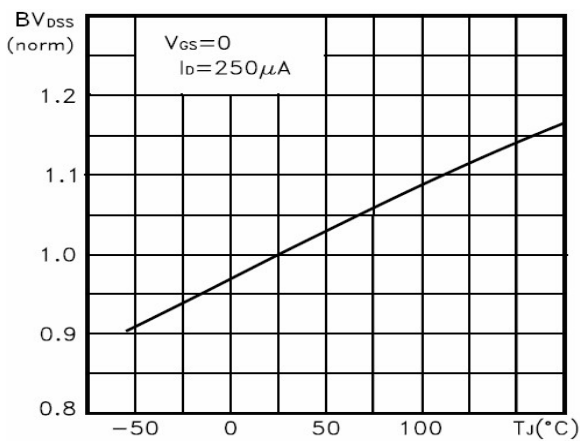


Figure 8: BVDSS vs Junction Temperature

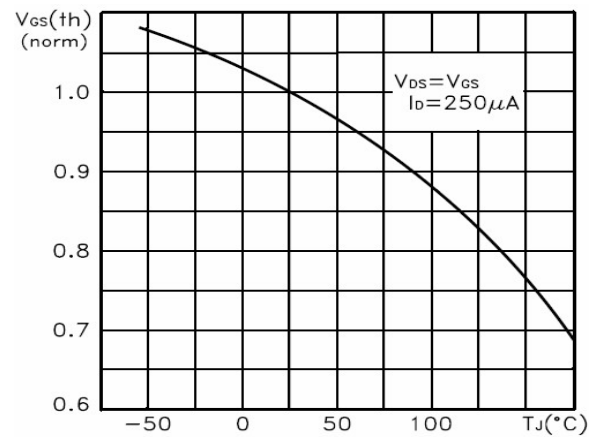
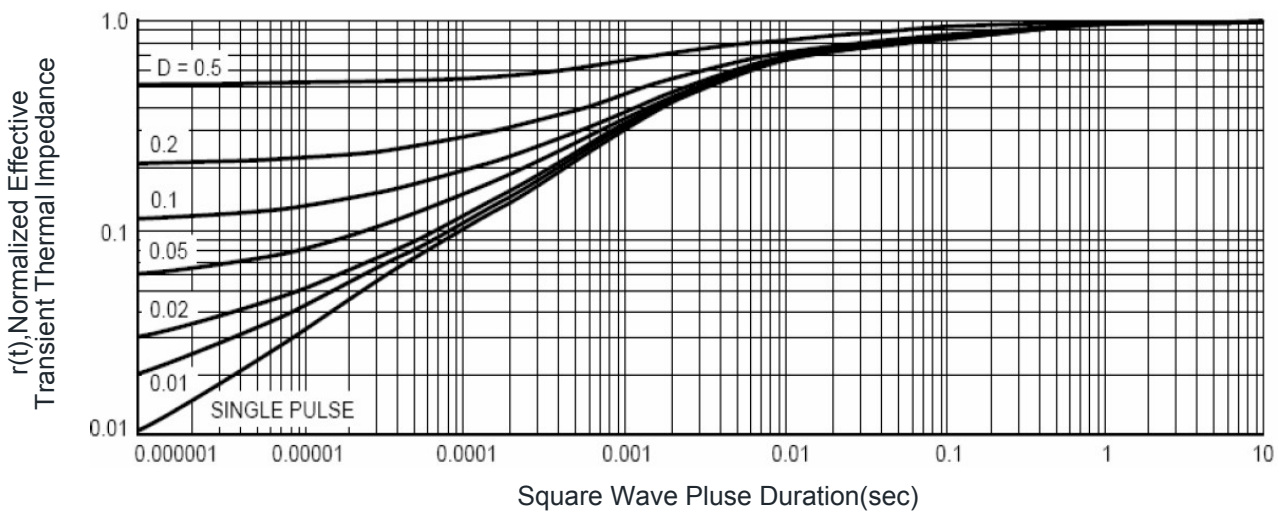


Figure 9: VGS(th) vs Junction Temperature





Test Circuit

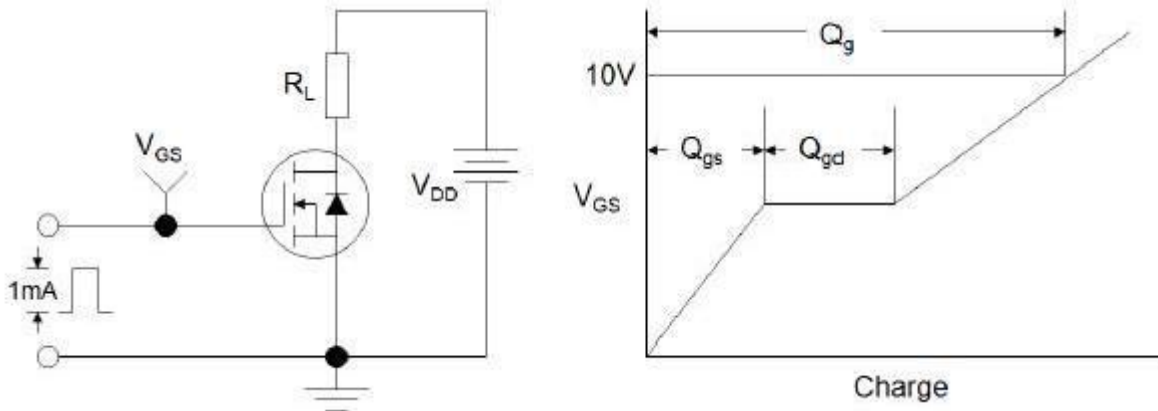


Figure1:Gate Charge Test Circuit & Waveform

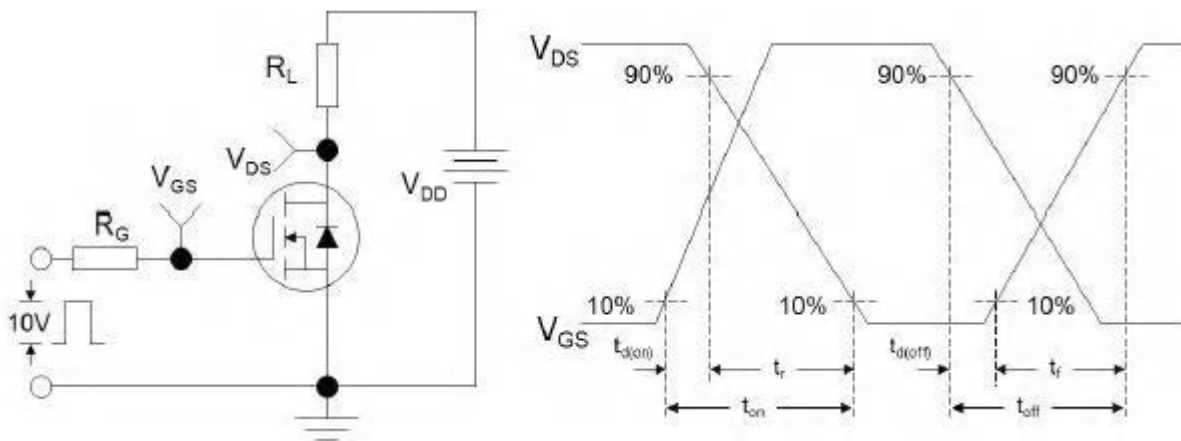


Figure 2: Resistive Switching Test Circuit & Waveforms

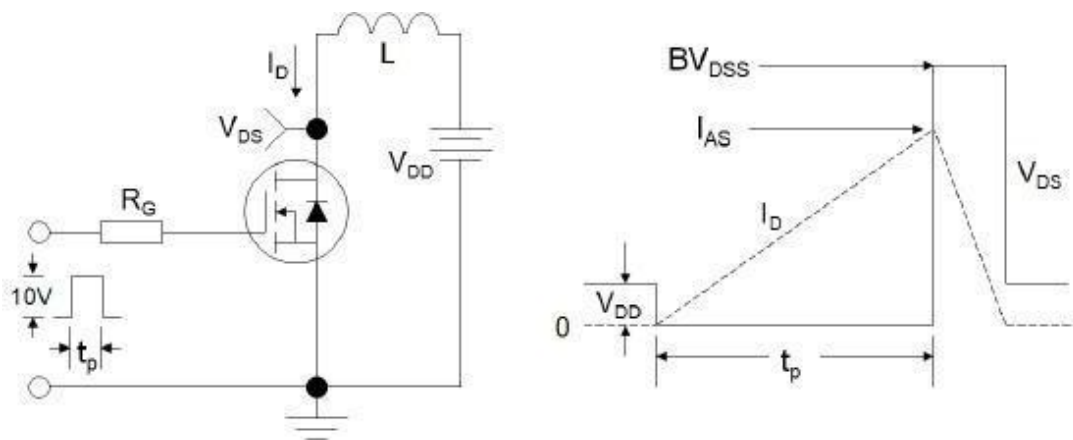
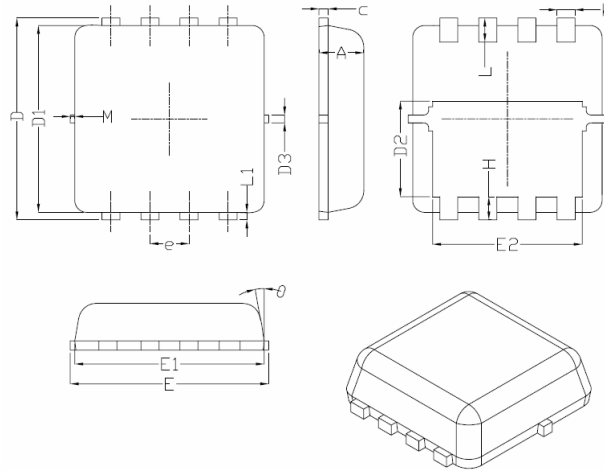


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



DFN3X3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°



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